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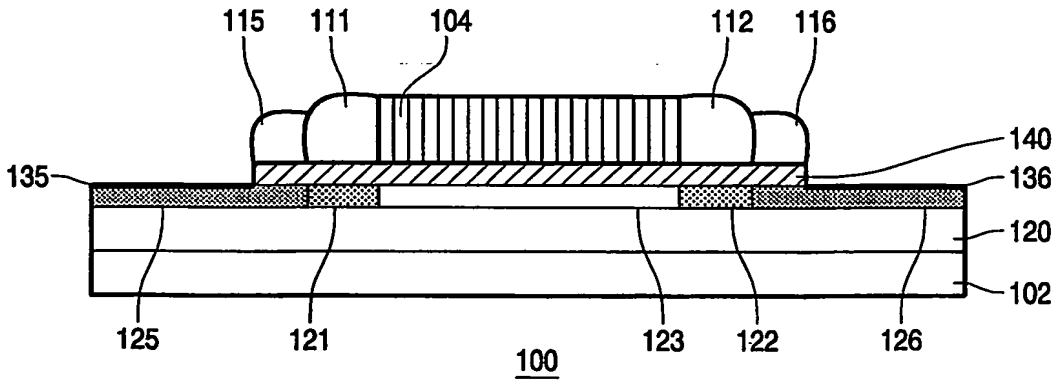
[Continued on next page]

(54) Title: THIN FILM TRANSISTOR, METHOD FOR PRODUCING A THIN FILM TRANSISTOR AND ELECTRONIC DEVICE HAVING SUCH A TRANSISTOR



(57) Abstract: A thin film transistor (100) is mounted on a substrate (102), which is covered by a semiconductor layer (120). The semiconductor layer (120) has a first doped region (121) and a second doped region (122) with an undoped region (123) in between. In addition, the semiconductor layer (120) has a first further doped region (125) and a second further doped region (126) forming the source and drain of the thin film transistor (100) and being more heavily doped than the first doped region (121) and the second doped region (122). A part of the semiconductor layer (120) is covered by an oxide layer (140), which carries a conductive gate (104) over the undoped region (130) and a first spacer (111) and second spacer (112) over the first doped region (121) and the second doped region (122) respectively. In addition, the oxide layer (140) carries a first insulating spacer (125) and a second insulating spacer (126) to provide adequate insulation between the gate structure and a first conducting contact (135) and a second conducting contact (136) respectively. Because the first spacer (111), the second spacer (112), the first insulating spacer (115) and the second insulating spacer (116) are mounted on the oxide layer (140), a thin film transistor (100) with favourable parasitic conductivity characteristics is obtained.

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